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Thyristor High Voltage, Phase Control SCR, 30 A



PRIMARY CHARACTERISTICS							
I _{T(AV)} 20 A							
V _{DRM} /V _{RRM}	1600 V						
V _{TM}	1.3 V						
I _{GT}	45 mA						
TJ	-40 °C to +125 °C						
Package	TO-247AC 3L						
Circuit configuration	Single SCR						

FEATURES

- High voltage (up to 1600 V)
- Designed and qualified according to JEDEC[®]-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding and battery charge

DESCRIPTION

The VS-30TPS16... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	20	А						
I _{RMS}		30	A						
V _{RRM} /V _{DRM}		1600	V						
I _{TSM}		300	А						
V _T	20 A, T _J = 25 °C	1.3	V						
dV/dt		500	V/µs						
dl/dt		150	A/µs						
TJ		-40 to +125	°C						

VOLTAGE RATINGS										
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA							
VS-30TPS16-M3	1600	1700	10							



FREE

VS-30TPS16-M3



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ABSOLUTE MAXIMUM RATING	ìS				
PARAMETER	SYMBOL	TEST COI	NDITIONS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	$T_{C} = 95 \ ^{\circ}C$, 180° conduction	half sine wave	20	
Maximum RMS on-state current	I _{RMS}		30	^	
Maximum peak, one-cycle,		10 ms sine pulse, rated V_{RRM}	applied	250	A
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage	reapplied	300	
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V_{RRM}	applied	310	A 2-
Maximum Pt for fusing	1-1	10 ms sine pulse, no voltage	442	A ² s	
Maximum I²√t for fusing	l²√t	t = 0.1 to 10 ms, no voltage r	4420	A²√s	
Maximum on-state voltage drop	V _{TM}	20 A, T _J = 25 °C	1.3	V	
On-state slope resistance	r _t	T 105.00		12	mΩ
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1.0	V
Maximum reverse and direct leakage	1 /1	T _J = 25 °C	$V_{\rm retad} V_{\rm r} \Delta V_{\rm r}$	0.5	
current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = rated V_{RRM}/V_{DRM}$	10	
Maximum holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C			mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V_{DRM} , R_g - k = open			V/µs
Maximum rate of rise of turned-on current	dl/dt			150	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
		Anode supply = 6 V, resistive load, T_J = -10 °C	60	mA	
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	45		
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	20		
		Anode supply = 6 V, resistive load, T_J = -10 °C	2.5		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	2.0	v	
		Anode supply = 6 V, resistive load, $T_J = 125 \text{ °C}$	1.0	v	
Maximum DC gate voltage not to trigger	V _{GD}	$T = 125 \circ 0$ V = rotad value	0.25		
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA	

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9						
Typical reverse recovery time	t _{rr}	T.I = 125 °C	4	μs					
Typical turn-off time	tq	1] = 125 0	110						

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VS-30TPS16-M3



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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to 125	°C				
Maximum thermal resistance, junction to case		R _{thJC}		0.8	°C/W				
Maximum thermal resistance, junction to ambient		R _{thJA}	DC operation	40					
Maximum thermal resistand case to heatsink	ce,	R _{thCS}	Mounting surface, smooth and greased	0.2					
Approximate weight				6	g				
Approximate weight				0.21	oz.				
Mounting torgue	minimum			6 (5)	kgf ⋅ cm				
Mounting torque	maximum			12 (10)	(lbf ⋅ in)				
Marking device	arking device		Case style TO-247AC 3L	30TF	PS16				

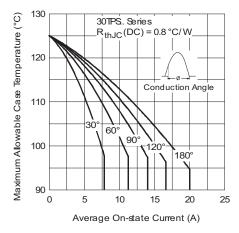


Fig. 1 - Current Rating Characteristics

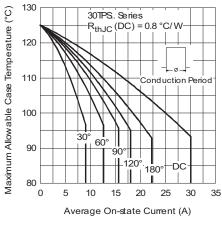


Fig. 2 - Current Rating Characteristics

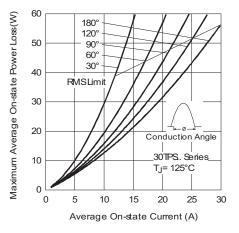


Fig. 3 - On-State Power Loss Characteristics

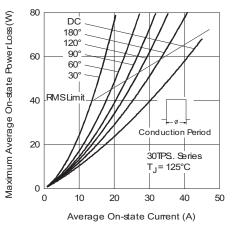


Fig. 4 - On-State Power Loss Characteristics

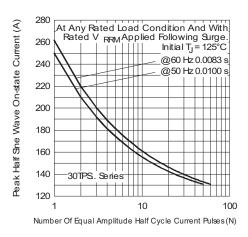
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Fig. 5 - Maximum Non-Repetitive Surge Current

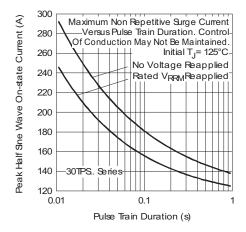


Fig. 6 - Maximum Non-Repetitive Surge Current

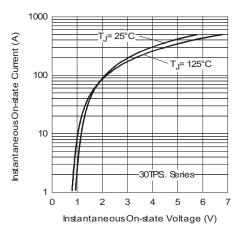


Fig. 7 - On-State Voltage Drop Characteristics

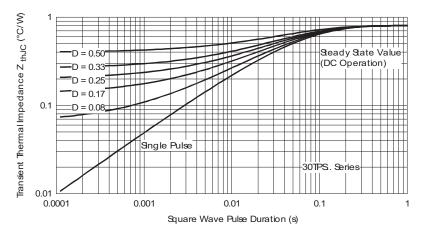


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

VS-30TPS16-M3

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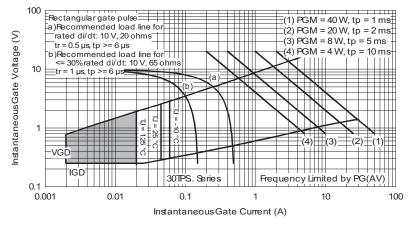


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

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SHA

Device code	VS-	30	т	Р	S	16	-M3
		2	3	4	5	6	7
	1 ·	· Visł	nay Sem	iconduc	tors pro	oduct	
	2 -	· Cur	rent rati	ng (30 =	30 A)		
	3 -	· Circ	uit conf	iguratio	n:		
			thyristo	r			
	4 -		kage:				
	5 -	-	TO-247. e of silic				
	5			d recove	erv rectit	fier	
	6 -			ng (16 =	-		
		Envi	ronmen	tal digit:			
		-M3	= halog	jen-free,	RoHS-	complia	int, and

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-30TPS16-M3	25	500	Antistatic plastic tubes					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?96138					
Part marking information	www.vishay.com/doc?95007					

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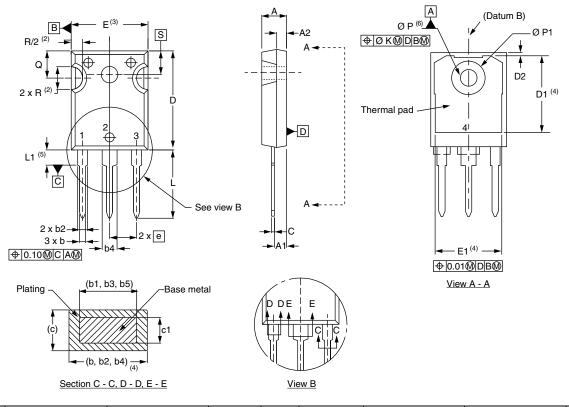
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TO-247AC 3L

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØК	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			ØΡ	3.56	3.66	0.14	0.144	
b5	2.59	3.38	0.102	0.133			Ø P1	-	7.39	-	0.291	
С	0.38	0.89	0.015	0.035			Q	5.31	5.69	0.209	0.224	
c1	0.38	0.84	0.015	0.033			R	4.52	5.49	0.178	0.216	
D	19.71	20.70	0.776	0.815	3		S	5.51	BSC	0.217	BSC	
D1	13.08	-	0.515	-	4							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension Q

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